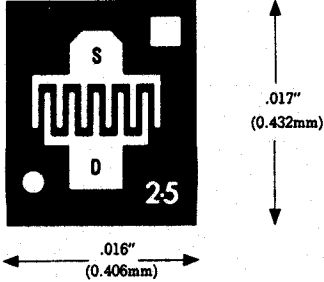


CHIP NUMBER  
**FN3.6**



Die Size: .16 x .17 (mils)  
0.406 x 0.432(mm)  
3 x 3 (mils)  
Pad Size: 0.076 x 0.076(mm)  
GATE-SUBSTRATE

**CONTACT METALLIZATION**

Top Contact: > 12,000  
Å Aluminum

Backside Contact: 3,000 Å Gold

**ASSEMBLY RECOMMENDATIONS**

It is advisable that:

- a) the die be eutectically mounted with gold silicon preform 98/2%.
- b) 1 mil (0.0254mm) aluminum wire be ultrasonically attached to the top contact.

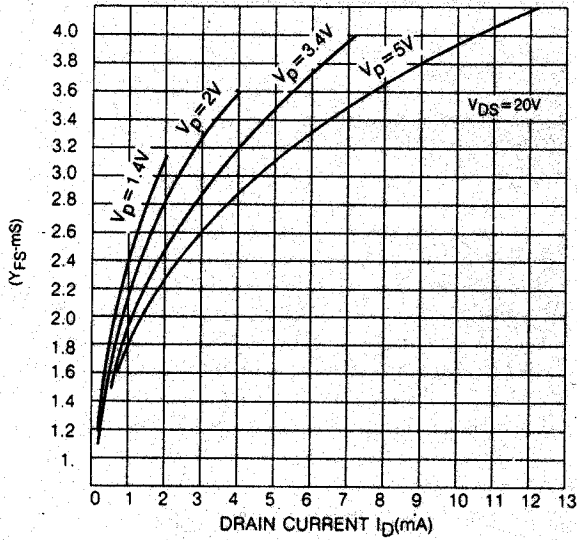
**TYPICAL ELECTRICAL CHARACTERISTICS**

PARAMETER	MIN.	TYP	MAX.	UNIT	TEST CONDITIONS
BV <sub>GSS</sub>	-30	-50	-70	V	V <sub>DS</sub> = 0, I <sub>G</sub> = 1μA
I <sub>DSS</sub>	0.5	8.0	20	mA	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0
g <sub>fs</sub>	1.5	4.0	6.0	mmho	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0
I <sub>GSS</sub>		25	100	pA	V <sub>GS</sub> = -30V, V <sub>DS</sub> = 0
r <sub>DS</sub>	150	200	600	Ω	V <sub>DS</sub> = 100mV, V <sub>GS</sub> = 0
V <sub>GS(off)</sub>	-1.0	-3.0	8.0	V	V <sub>DS</sub> = 15V, I <sub>D</sub> = 1nA
C <sub>rss</sub>	1.2	2.0	3.0	pF	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0, f = 1MHz
C <sub>iss</sub>		4.5	6.0	pF	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0, f = 1MHz

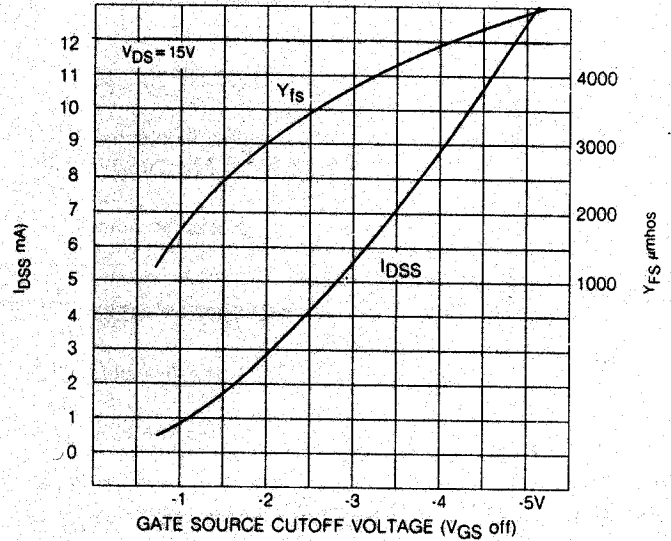
TYPICAL DEVICE TYPES: 2N3821 - 2N3824, 2N3921 - 2N3922, 2N5545 - 2N5547

**CHIP TYPE FN3.6**

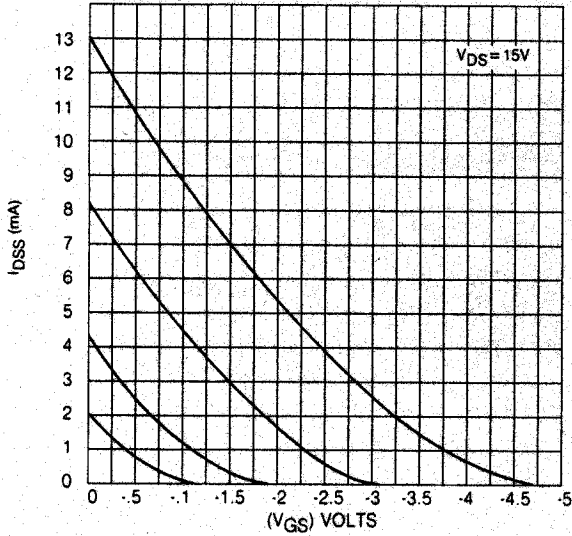
**FORWARD TRANSADMITTANCE VS. OPERATING DRAIN CURRENT**



**FORWARD TRANSADMITTANCE VS.**



**TRANSFER CHARACTERISTICS**



**OUTPUT CHARACTERISTICS**

